

isc Silicon NPN Power Transistor

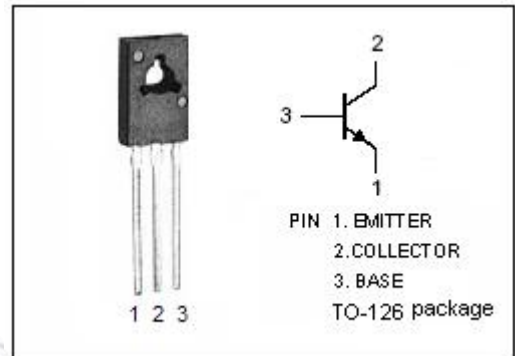
2SD1619

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 25V$ (Min)
- Complement to Type 2SB1119
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

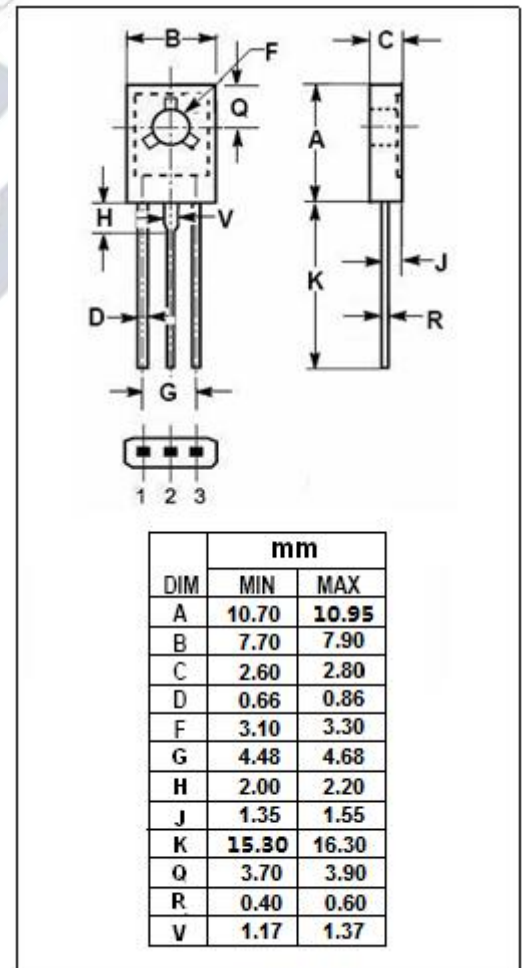
APPLICATIONS

- Designed for L_F Amp Electronic Governor applications.



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	25	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	1	A
I_{CM}	Collector Current-Peak	2	A
P_C	Collector Power Dissipation @ $T_c=25^\circ C$	0.5	W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-55~150	°C



isc Silicon NPN Power Transistor**2SD1619****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=1\text{mA}; I_B=0$	25			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=-10\mu\text{A}; I_E=0$	25			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=10\mu\text{A}; I_C=0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=500\text{mA}; I_B=50\text{mA}$			0.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=500\text{mA}; I_B=50\text{mA}$			1.2	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=20\text{V}; I_E=0$			0.1	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=4\text{V}; I_C=0$			0.1	μA
h_{FE-1}	DC Current Gain	$I_C=50\text{mA}; V_{CE}=2\text{V}$	100		560	
h_{FE-2}	DC Current Gain	$I_C=1\text{A}; V_{CE}=2\text{V}$	40			
f_T	Current-Gain—Bandwidth Product	$I_C=50\text{mA}; V_{CE}=10\text{V}$		180		MHz
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f=1.0\text{MHz}$		15		pF

◆ **h_{FE-1} Classifications**

R	S	T	U
100-200	140-280	200-400	280-560